

## Prof. MEHMET KASAP

### Personal Information

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### International Researcher IDs

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Publons / Web Of Science ResearcherID: AHE-8287-2022

Yoksis Researcher ID: 2692

### Education Information

Doctorate, University of Surrey, United Kingdom 1990 - 1994

Postgraduate, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), Turkey 1985 - 1989

Undergraduate, Firat University, Faculty Of Arts And Sciences, Fizik Mühendisliği Pr., Turkey 1981 - 1985

### Dissertations

Doctorate, Temperature and Pressure Dependent of Electron Transport in Plasticly Relaxed  $In_xGa_{1-x}As$ , University of Surrey, 1994

Postgraduate, Enerji band hesaplamalarında APW metodu ve bazı geçiş elementlerine uygulanması, Gazi University, Fen Bilimleri Enstitüsü, Fizik (YI) (Tezli), 1988

### Research Areas

Surfaces, Interfaces, Thin Films and Nanosystems, Electronic structure of bulk material, Electrical properties of electronic structures, interfaces, thin films and low-dimensional structures, Magnetic Properties and Materials, Optical Properties, Spectroscopy of Matter, Electronic transport in condensed matter

### Academic Titles / Tasks

Professor, Gazi University, Fen Fakültesi, Fizik, 2006 - Continues

Professor, Gazi University, Fen Fakültesi, Fizik, 2000 - 2006

Assistant Professor, Gazi University, Fen Fakültesi, Fizik, 1996 - 2000

Research Assistant, Gazi University, Fen Fakültesi, Fizik, 1985 - 1996

### Courses

YARIİLETKEN FİZİĞİ, Undergraduate, 2017 - 2018, 2016 - 2017

TEMEL FİZİK II (ELEKTRİK), Undergraduate, 2017 - 2018

Maddenin Özellikleri, Undergraduate, 2017 - 2018

YARIİLETKEN FİZİĞİ, Postgraduate, 2017 - 2018, 2016 - 2017

## Advising Theses

- KASAP M., The Fabrication Of Au/(Mgo-Pvp) /N-Si (Mps) Schottky Barrier Diodes And The Investigation Their Electrical And Dielectrical Properties, Doctorate, A.EROĞLU(Student), 2021
- KASAP M., Investigation Of Structural And Electrical Properties Of Zno Thin Films By Mist Chemical Vapor Deposition Method On Sapphire With Different Orientation, Postgraduate, M.YAYLA(Student), 2021
- KASAP M., Forensic Sciences In Terms Of Shot Residue Analysis Techniques And Forensic Applications, Doctorate, İ.KARA(Student), 2014
- KASAP M., Electron Transport Properties Of Ingan And Gan Quantum Well Inaln/Gan High Electron Mobility Transistor, Postgraduate, P.NARİN(Student), 2014
- KASAP M., The investigation of temperature dependent electrical transport properties of InxGa1-xP/GaAs, Postgraduate, E.BOYALI(Student), 2013
- KASAP M., Temperature dependent electrical properties of high doped InxGa1-xAs alloy semiconductor, Postgraduate, E.YAZBAHAR(Student), 2012
- KASAP M., Electron and magnetotransport properties of inaln/gan based high electron mobility transistors (HEMT), Doctorate, P.TUNAY(Student), 2010
- KASAP M., AlGaN/GaN temelli yüksek elektron hareketlilikli transistörlerin (HEMT) elektron ve manyeto iletim özellikleri, Doctorate, S.BORA(Student), 2008
- KASAP M., ELECTRON TRANSPORT PROPERTIES OF InxGa1-xN, Doctorate, A.YILDIZ(Student), 2008
- KASAP M., AlGaN/GaN TEMELLİ YÜKSEK ELEKTRON HAREKETLİLİKLİ TRANSİSTÖRLERİN (HEMT) ELEKTRON VE MANYETO İLETİM ÖZELLİKLERİ, Doctorate, S.Bora(Student), 2008
- KASAP M., LEC tekniği ile büyütülen Zn katkılı InAs yarıiletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Postgraduate, İ.KARA(Student), 2006
- KASAP M., MBE tekniği ile büyütülen InGaAs/GaAs ve AlGaAs yarıiletkenlerinin iletim özellikleri, Postgraduate, S.BORA(Student), 2005
- KASAP M., LEC tekniği ile büyütülen Te katkılı n-Tipi InSb yarıiletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Postgraduate, Ü.YURDUGÜL(Student), 2005
- KASAP M., GaN yarıiletken kristalinde elektron iletimi, Postgraduate, A.YILDIZ(Student), 2004
- KASAP M., InAs yarıiletken kristalinde elektron iletimi, Postgraduate, D.DEMİR(Student), 2004
- KASAP M., LEC tekniği ile büyütülen bulk InAs yarıiletkenin magneto ve elektron iletim özellikleri, Postgraduate, N.KEREM(Student), 2004
- KASAP M., LEC tekniği ile büyütülen Te katkılı n-tipi GaSb yarı iletkeninde sıcaklık bağımlı manyetik ve elektron iletim özellikleri, Postgraduate, B.YASEMİN(Student), 2004
- KASAP M., GaAs ve InP yarıiletkenlerde elektriksel karakterizasyon, Doctorate, S.ACAR(Student), 2003
- KASAP M., In0.51Ga0.49As ve In0.60Ga0.40As yarıiletkenlerinde mobilite hesaplamaları, Postgraduate, S.DEMİREZEN(Student), 2001

## Published journal articles indexed by SCI, SSCI, and AHCI

- I. **Temperature dependent electron transport properties of degenerate SnO<sub>2</sub> thin films**  
Boyalı E., Baran V., ASAR T., Ozcelik S., Kasap M.  
JOURNAL OF ALLOYS AND COMPOUNDS, vol.692, pp.119-123, 2017 (SCI-Expanded)
- II. **Evaluation of morphological and chemical differences of gunshot residues in different ammunitions using SEM/EDS technique**  
Kara I., Sarikavak Y., LIŞESİVDİN S. B., KASAP M.  
ENVIRONMENTAL FORENSICS, vol.17, no.1, pp.68-79, 2016 (SCI-Expanded)
- III. **The Relationship Between the Surface Morphology and Chemical Composition of Gunshot Residue**

## Particles

Kara I, LİŞESİVDİN S. B., Kasap M., Er E., Uzek U.

JOURNAL OF FORENSIC SCIENCES, vol.60, no.4, pp.1030-1033, 2015 (SCI-Expanded)

- IV. **Electron Transport Properties of Two-Dimensional Electron Gas in  $\text{Be}_x\text{Zn}_{1-x}\text{O}/\text{ZnO}$  Heterostructures**  
Atmaca G., Narin P., Lisesivdin S. B., Kasap M., Sarikavak-Lisesivdin B.  
PHILOSOPHICAL MAGAZINE, vol.95, no.1, pp.79-89, 2015 (SCI-Expanded)
- V. **Analysis Of The Number Of Shots Using Graphite Furnace Atomic Absorption Spectrometry On The Gunshot Residues Deposited in The Barrel**  
KARA İ., YALÇINKAYA Ö., LİŞESİVDİN S. B., KASAP M.  
SYLWAN, vol.159, no.1, pp.14-26, 2015 (SCI-Expanded)
- VI. **Study on growth and characterizations of  $\text{Ga}_{1-x}\text{In}_x\text{P}/\text{GaAs}$  solar cell structure**  
Kınacı B., Özen Y., Asar T., Cetin S. Ş., Memmedli T., Kasap M., Ozcelik S.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.24, no.9, pp.3269-3274, 2013 (SCI-Expanded)
- VII. **Investigation of  $\text{AlInN}$  HEMT structures with different  $\text{AlGaIn}$  buffer layers grown on sapphire substrates by MOCVD**  
Kelekci O., Tasli P., Cetin S. Ş., Kasap M., Ozcelik S., Ozbay E.  
CURRENT APPLIED PHYSICS, vol.12, no.6, pp.1600-1605, 2012 (SCI-Expanded)
- VIII. **Electron transport properties in  $\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}/\text{AlN}/\text{GaN}$  heterostructures with different  $\text{InGaIn}$  back barrier layers and  $\text{GaN}$  channel thicknesses grown by MOCVD**  
Kelekci O., Tasli P. T., Yu H., KASAP M., ÖZÇELİK S., ÖZBAY E.  
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, vol.209, no.3, pp.434-438, 2012 (SCI-Expanded)
- IX. **Epitaxial growth and electrical characterization of germanium**  
Bosi M., Attolini G., Ferrari C., Frigeri C., Calicchio M., Gombia E., Asar T., Boyali E., Aydemir U., Ozcelik S., et al.  
CRYSTAL RESEARCH AND TECHNOLOGY, vol.46, no.8, pp.813-817, 2011 (SCI-Expanded)
- X. **Grain Boundary Related Electrical Transport in Al-rich  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  Layers Grown by Metal-Organic Chemical Vapor Deposition**  
Yildiz A., Tasli P., Sarikavak B., Lisesivdin S. B., Ozturk M. K., Kasap M., Ozcelik S., Ozbay E.  
SEMICONDUCTORS, vol.45, no.1, pp.33-36, 2011 (SCI-Expanded)
- XI. **Electron-Electron Interactions in Sb-Doped  $\text{SnO}_2$  Thin Films**  
Serin T., Yildiz A., SERİN N., Yildirim N., Ozyurt F., KASAP M.  
JOURNAL OF ELECTRONIC MATERIALS, vol.39, no.8, pp.1152-1158, 2010 (SCI-Expanded)
- XII. **The substrate temperature dependent electrical properties of titanium dioxide thin films**  
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.  
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.21, no.7, pp.692-697, 2010 (SCI-Expanded)
- XIII. **Double subband occupation of the two-dimensional electron gas in  $\text{In}_x\text{Al}_{1-x}\text{N}/\text{AlN}/\text{GaN}/\text{AlN}$  heterostructures with a low indium content ( $0.064 \leq x \leq 0.140$ ) barrier**  
LİŞESİVDİN S. B., Tasli P., Kasap M., Ozturk M., Arslan E., Ozcelik S., Ozbay E.  
THIN SOLID FILMS, vol.518, no.19, pp.5572-5575, 2010 (SCI-Expanded)
- XIV. **Scattering analysis of two-dimensional electrons in  $\text{AlGaIn}/\text{GaN}$  with bulk related parameters extracted by simple parallel conduction extraction method**  
Lisesivdin S. B., Yildiz A., Balkan N., Kasap M., Ozcelik S., Ozbay E.  
JOURNAL OF APPLIED PHYSICS, vol.108, no.1, 2010 (SCI-Expanded)
- XV. **Determination of the critical indium composition corresponding to the metal-insulator transition in  $\text{In}_x\text{Ga}_{1-x}\text{N}$  ( $0.06 \leq x \leq 0.135$ ) layers**  
Yildiz A., LİŞESİVDİN S. B., Tasli P., Ozbay E., Kasap M.  
CURRENT APPLIED PHYSICS, vol.10, no.3, pp.838-841, 2010 (SCI-Expanded)
- XVI. **The temperature dependence of the inelastic scattering time in  $\text{InGaIn}$  grown by MOVPE**  
Yildiz A., Kasap M.  
LOW TEMPERATURE PHYSICS, vol.36, no.4, pp.320-324, 2010 (SCI-Expanded)

- XVII. **Analysis of defect related optical transitions in biased AlGa<sub>N</sub>/Ga<sub>N</sub> heterostructures**  
 Bengi A., LİŞESİVDİN S. B., Kasap M., Mammadov T., Ozcelik S., Ozbay E.  
 MATERIALS SCIENCE IN SEMICONDUCTOR PROCESSING, vol.13, no.2, pp.105-108, 2010 (SCI-Expanded)
- XVIII. **The thickness effect on the electrical conduction mechanism in titanium oxide thin films**  
 Yildiz A., Serin N., Kasap M., Serin T., Mardare D.  
 JOURNAL OF ALLOYS AND COMPOUNDS, vol.493, pp.227-232, 2010 (SCI-Expanded)
- XIX. **Investigation of low-temperature electrical conduction mechanisms in highly resistive Ga<sub>N</sub> bulk layers extracted with Simple Parallel Conduction Extraction Method**  
 Yildiz A., LİŞESİVDİN S. B., Kasap M., Ozcelik S., Ozbay E., Balkan N.  
 APPLIED PHYSICS A-MATERIALS SCIENCE & PROCESSING, vol.98, no.3, pp.557-563, 2010 (SCI-Expanded)
- XX. **Well parameters of two-dimensional electron gas in Al<sub>0.88</sub>In<sub>0.12</sub>N/Al<sub>N</sub>/Ga<sub>N</sub>/Al<sub>N</sub> heterostructures grown by MOCVD**  
 Tasli P., LİŞESİVDİN S. B., Yildiz A., Kasap M., Arslan E., Ozcelik S., Ozbay E.  
 CRYSTAL RESEARCH AND TECHNOLOGY, vol.45, no.2, pp.133-139, 2010 (SCI-Expanded)
- XXI. **Contributions of impurity band and electron-electron interactions to magnetoconductance in AlGa<sub>N</sub>**  
 Tasli P., Yildiz A., Kasap M., Ozbay E., LİŞESİVDİN S. B., Ozcelik S.  
 PHILOSOPHICAL MAGAZINE, vol.90, no.26, pp.3591-3599, 2010 (SCI-Expanded)
- XXII. **Electrical conduction properties of Si delta-doped GaAs grown by MBE**  
 Yildiz A., LİŞESİVDİN S. B., Altuntas H., Kasap M., Ozcelik S.  
 PHYSICA B-CONDENSED MATTER, vol.404, no.21, pp.4202-4206, 2009 (SCI-Expanded)
- XXIII. **Crossover from Nearest-Neighbor Hopping Conduction to Efros-Shklovskii Variable-Range Hopping Conduction in Hydrogenated Amorphous Silicon Films**  
 Yildiz A., SERİN N., Serin T., KASAP M.  
 JAPANESE JOURNAL OF APPLIED PHYSICS, vol.48, no.11, 2009 (SCI-Expanded)
- XXIV. **The effect of intrinsic defects on the hole transport in Cu<sub>2</sub>O**  
 Yildiz A., Serin N., Serin T., Kasap M.  
 OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.3, no.10, pp.1034-1037, 2009 (SCI-Expanded)
- XXV. **Structural, electrical and optical characterization of InGa<sub>N</sub> layers grown by MOVPE**  
 Yildiz A., Kemal O. M., Bosi M., Ozcelik S., Kasap M.  
 CHINESE PHYSICS B, vol.18, no.9, pp.4007-4012, 2009 (SCI-Expanded)
- XXVI. **DX-center energy calculation with quantitative mobility spectrum analysis in n-AlGaAs/GaAs structures with low Al content**  
 LİŞESİVDİN S. B., Altuntas H., Yildiz A., Kasap M., Ozbay E., Ozcelik S.  
 SUPERLATTICES AND MICROSTRUCTURES, vol.45, no.6, pp.604-611, 2009 (SCI-Expanded)
- XXVII. **Numerical optimization of Al-mole fractions and layer thicknesses in normally-on AlGa<sub>N</sub>-Ga<sub>N</sub> double-channel high electron mobility transistors (DCHEMTs)**  
 Atmaca G., Elıbol K., LİŞESİVDİN S. B., Kasap M., Ozbay E.  
 JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, vol.11, no.5, pp.578-582, 2009 (SCI-Expanded)
- XXVIII. **Large zero-field spin splitting in AlGa<sub>N</sub>/Al<sub>N</sub>/Ga<sub>N</sub>/Al<sub>N</sub> heterostructures**  
 LİŞESİVDİN S. B., Balkan N., Makarovskiy O., Patane A., Yildiz A., Caliskan M. D., Kasap M., Ozcelik S., Ozbay E.  
 JOURNAL OF APPLIED PHYSICS, vol.105, no.9, 2009 (SCI-Expanded)
- XXIX. **Non-adiabatic small polaron hopping conduction in Nb-doped TiO<sub>2</sub> thin film**  
 Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.  
 PHYSICA B-CONDENSED MATTER, vol.404, pp.1423-1426, 2009 (SCI-Expanded)
- XXX. **Anomalous temperature dependence of the electrical resistivity in In<sub>0.17</sub>Ga<sub>0.83</sub>N**  
 Yildiz A., LİŞESİVDİN S. B., Kasap M., Bosi M.  
 SOLID STATE COMMUNICATIONS, vol.149, pp.337-340, 2009 (SCI-Expanded)
- XXXI. **Comparison of the transport properties of high quality AlGa<sub>N</sub>/Al<sub>N</sub>/Ga<sub>N</sub> and AlIn<sub>N</sub>/Al<sub>N</sub>/Ga<sub>N</sub> two-dimensional electron gas heterostructures**  
 TÜLEK R., ILGAZ A., GÖKDEN S., TEKE A., Ozturk M. K., KASAP M., Ozcelik S., Arslan E., ÖZBAY E.

- JOURNAL OF APPLIED PHYSICS, vol.105, no.1, 2009 (SCI-Expanded)
- XXXII. **Electrical properties of TiO(2) thin films**  
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.  
JOURNAL OF NON-CRYSTALLINE SOLIDS, vol.354, pp.4944-4947, 2008 (SCI-Expanded)
- XXXIII. **Growth parameter investigation of Al<sub>0.25</sub>Ga<sub>0.75</sub>N/GaN/AlN heterostructures with Hall effect measurements**  
LİŞESİVDİN S. B., Demirezen S., Caliskan M. D., Yildiz A., Kasap M., Ozcelik S., Ozbay E.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, vol.23, no.9, 2008 (SCI-Expanded)
- XXXIV. **The persistent photoconductivity effect in AlGa<sub>x</sub>N/GaN heterostructures grown on sapphire and SiC substrates**  
Arslan E., Butun S., LİŞESİVDİN S. B., KASAP M., ÖZÇELİK S., ÖZBAY E.  
JOURNAL OF APPLIED PHYSICS, vol.103, no.10, 2008 (SCI-Expanded)
- XXXV. **Stokes shift and band gap bowing in In<sub>x</sub>Ga<sub>1-x</sub>N (0.060 ≤ x ≤ 0.105) grown by metalorganic vapour phase epitaxy**  
Yildiz A., Dagdelen F., ACAR S., LİŞESİVDİN S. B., Kasap M., AYDOĞDU Y., Bosi M.  
ACTA PHYSICA POLONICA A, vol.113, no.2, pp.731-739, 2008 (SCI-Expanded)
- XXXVI. **Determination of two-dimensional electron and hole gas carriers in AlGa<sub>x</sub>N/GaN/AlN heterostructures grown by Metal Organic Chemical Vapor Deposition**  
ACAR S., LİŞESİVDİN S. B., Kasap M., Oezcelik S., Ozbay E.  
THIN SOLID FILMS, vol.516, no.8, pp.2041-2044, 2008 (SCI-Expanded)
- XXXVII. **Self-consistent scattering analysis of Al<sub>0.2</sub>Ga<sub>0.8</sub>N/AlN/GaN/AlN heterostructures grown on 6H-SiC substrates using photo-Hall effect measurements**  
LİŞESİVDİN S. B., Arslan E., Kasap M., Ozcelik S., Ozbay E.  
JOURNAL OF PHYSICS-CONDENSED MATTER, vol.20, no.4, 2008 (SCI-Expanded)
- XXXVIII. **The effect of strain relaxation on electron transport in undoped Al<sub>0.25</sub>Ga<sub>0.75</sub>N/GaN heterostructures**  
LİŞESİVDİN S. B., Yildiz A., ACAR S., Kasap M., Oezcelik S., Ozbay E.  
PHYSICA B-CONDENSED MATTER, vol.399, no.2, pp.132-137, 2007 (SCI-Expanded)
- XXXIX. **Electron transport in Ga-rich In<sub>x</sub>Ga<sub>1-x</sub>N alloys**  
Yildiz A., LİŞESİVDİN S. B., ACAR S., Kasap M., Bosi M.  
CHINESE PHYSICS LETTERS, vol.24, no.10, pp.2930-2933, 2007 (SCI-Expanded)
- XL. **Electronic transport characterization of AlGa<sub>x</sub>N/GaN heterostructures using quantitative mobility spectrum analysis**  
LİŞESİVDİN S. B., Yildiz A., ACAR S., Kasap M., Ozcelik S., Ozbay E.  
APPLIED PHYSICS LETTERS, vol.91, no.10, 2007 (SCI-Expanded)
- XLI. **Temperature-dependent electron transport in In<sub>0.5</sub>Ga<sub>0.5</sub>P/GaAs grown by MOVPE**  
ACAR S., Yildiz A., Kasap M., Bosi M.  
CHINESE PHYSICS LETTERS, vol.24, no.8, pp.2373-2375, 2007 (SCI-Expanded)
- XLII. **Scattering analysis of 2DEG carrier extracted by QMSA in undoped Al<sub>0.25</sub>Ga<sub>0.75</sub>N/GaN heterostructures**  
LİŞESİVDİN S. B., ACAR S., Kasap M., Ozcelik S., Gokden S., Ozbay E.  
SEMICONDUCTOR SCIENCE AND TECHNOLOGY, vol.22, no.5, pp.543-548, 2007 (SCI-Expanded)
- XLIII. **High temperature variable-range hopping conductivity in undoped TiO<sub>2</sub> thin film**  
Yildiz A., LİŞESİVDİN S. B., Kasap M., Mardare D.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.1, no.10, pp.531-533, 2007 (SCI-Expanded)
- XLIV. **Optimization of alloy composition, interlayer and barrier thicknesses in Al<sub>x</sub>Ga<sub>1-x</sub>N/(AlN)/GaN high electron mobility transistors**  
LİŞESİVDİN S. B., Yildiz A., Kasap M.  
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, vol.1, no.9, pp.467-470, 2007 (SCI-Expanded)

- XLV. **Quantitative mobility spectrum analysis for determination of electron and magneto transport properties of Te-doped GaSb**  
ACAR S., Kasap M., Isik B., Ozcelik S., Tugluoglu N., Karadeniz S.  
Chinese Physics Letters, vol.22, no.9, pp.2363-2366, 2005 (SCI-Expanded)
- XLVI. **Temperature-dependent galvanomagnetic measurements on doped InSb and InAs grown by liquid encapsulated czochralski**  
Kasap M., ACAR S., Ozcelik S., Karadeniz S., Tugluoglu N.  
Chinese Physics Letters, vol.22, no.5, pp.1218-1221, 2005 (SCI-Expanded)
- XLVII. **The temperature dependence of electron and magneto transport properties in Te-doped InSb**  
Kasap M., ACAR S.  
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, vol.201, no.14, pp.3113-3120, 2004 (SCI-Expanded)
- XLVIII. **Temperature-dependent barrier characteristics of inhomogeneous in/p-Si (100) Schottky barrier diodes**  
Tugluoglu N., Karadeniz S., ACAR S., Kasap M.  
CHINESE PHYSICS LETTERS, vol.21, no.9, pp.1795-1798, 2004 (SCI-Expanded)
- XLIX. **Gaussian distribution of inhomogeneous barrier height in Ag/p-Si (100) Schottky barrier diodes**  
ACAR S., Karadeniz S., Tugluoglu N., Selcuk A., Kasap M.  
APPLIED SURFACE SCIENCE, vol.233, pp.373-381, 2004 (SCI-Expanded)
- L. **Conductivity, Hall and magnetoresistance effect measurements on SiGaAs and InP**  
ACAR S., Kasap M.  
PHYSICA STATUS SOLIDI A-APPLIED RESEARCH, vol.201, no.7, pp.1551-1557, 2004 (SCI-Expanded)
- LI. **Prebreakdown current behaviour in the ionization cell with a semiconductor cathode**  
Salamov B., Kasap M., Lebedeva N.  
JOURNAL OF PHYSICS D-APPLIED PHYSICS, vol.33, no.17, pp.2192-2195, 2000 (SCI-Expanded)
- LII. **The simulation of the two-dimensional Ising model in the presence of an external magnetic field on the Creutz cellular automaton**  
Kutlu B., Kasap M., Turan S.  
INTERNATIONAL JOURNAL OF MODERN PHYSICS C, vol.11, no.3, pp.561-572, 2000 (SCI-Expanded)
- LIII. **The concentration of currents on the artificial surface inhomogeneities of semiconducting cathodes in ionization cells**  
Salamov B., Ozer M., Kasap M., Altindal Ş.  
JOURNAL OF PHYSICS D-APPLIED PHYSICS, vol.32, no.6, pp.682-687, 1999 (SCI-Expanded)
- LIV. **The temperature and pressure dependence of electron transport in plastically relaxed In<sub>x</sub>Ga<sub>1-x</sub>As**  
Kasap M., Lancefield D.  
PHYSICA STATUS SOLIDI B-BASIC RESEARCH, vol.199, no.2, pp.481-493, 1997 (SCI-Expanded)
- LV. **The rapid visualization of resistivity inhomogeneities in high-resistivity semiconductor films**  
Salamov B., Civi M., Altindal Ş., Kasap M., BULUR E.  
JOURNAL OF INFORMATION RECORDING, vol.23, no.5, pp.437-445, 1997 (SCI-Expanded)
- LVI. **Impurity conduction in In<sub>x</sub>Ga<sub>1-x</sub>As**  
KASAP M., ÖZER M., Çolakoğlu K.  
Turkish Journal of Physics, vol.20, no.7, pp.740-746, 1996 (SCI-Expanded)

### Refereed Congress / Symposium Publications in Proceedings

- I. **Determination of Structural and Electrical Properties of ZnO Thin Films Grown By Mist-Cvd Method on Sapphire with Different Orientations**  
Yayla M., LİŞESİVDİN S. B., KASAP M.  
Turkish Physical Society 37th International Physics Congress, Muğla, Turkey, 01 September 2021, pp.236
- II. **The Study on Antimony Diffusion in Gallium-Doped Germanium Grown by Chochralski Technique**

- Baran V., Çat Y., Akın Sönmez N., Özen Y., Kasap M., Özçelik S.  
Turkish Physical Society 33th International Physics Congress, Muğla, Turkey, 6 - 10 September 2017
- III. **The Study on Antimony Diffusion in Gallium-doped Germanium Grown by Czochralski Technique**  
Baran V., Çat Y., Akın Sönmez N., Özen Y., Kasap M., Özçelik S.  
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- IV. **Pt Metal Kümelerin Katkısız SnO<sub>2</sub> Sensör Yapılarının Algılama Özelliklerine Etkisi**  
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